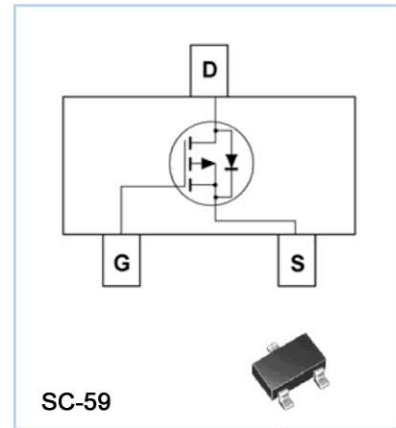


## P-Channel Enhancement Mode MOSFET Feature

- -30V/-4.2A,  $R_{DS(ON)} = 130\text{m}\Omega$  (MAX) @ $V_{GS} = -10\text{V}$ .  
 $R_{DS(ON)} = 150\text{m}\Omega$  (MAX) @ $V_{GS} = -4.5\text{V}$ .  
 $R_{DS(ON)} = 180\text{m}\Omega$  (MAX) @ $V_{GS} = -2.5\text{V}$ .
- Super High dense cell design for extremely low  $R_{DS(ON)}$
- Reliable and Rugged
- SC-59 for Surface Mount Package



## Applications

- Power Management  
 Portable Equipment and Battery Powered Systems.

## Absolute Maximum Ratings $T_A=25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$I_D$	-4.2	A

## Electrical Characteristics $T_A=25^\circ\text{C}$ Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
<b>Off Characteristics</b>						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS}=0\text{V}, I_D=-250\mu\text{A}$	-30	-	-	V
Zero-Gate Voltage Drain Current	IDSS	$V_{DS}=-24\text{V}, V_{GS}=0\text{V}$	-	-	-1	$\mu\text{A}$
Gate Body Leakage Current, Forward	IGSSF	$V_{GS}=12\text{V}, V_{DS}=0\text{V}$	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	$V_{GS}=-12\text{V}, V_{DS}=0\text{V}$	-	-	-100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=-250\mu\text{A}$	-0.7	-	-1.3	V
Static Drain-source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10\text{V}, I_D=-4.2\text{A}$	-	-	130	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}, I_D=-4.0\text{A}$	-	-	150	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}, I_D=-1.0\text{A}$	-	-	180	$\text{m}\Omega$
		<b>Drain-Source Diode Characteristics and Maximum Ratings</b>				
Drain-Source Diode Forward Voltage	VSD	$V_{GS}=0\text{V}, I_S=-1.0\text{A}$			-1.0	V

## Typical Characteristics

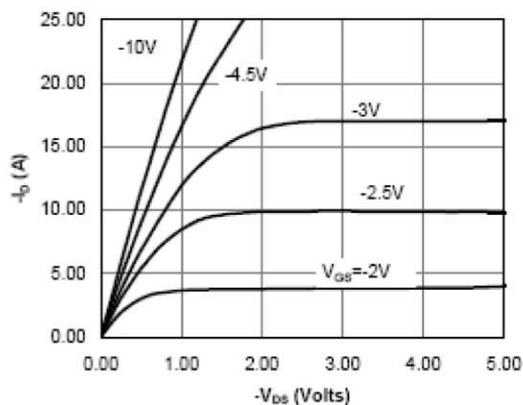


Fig 1: On-Region Characteristics

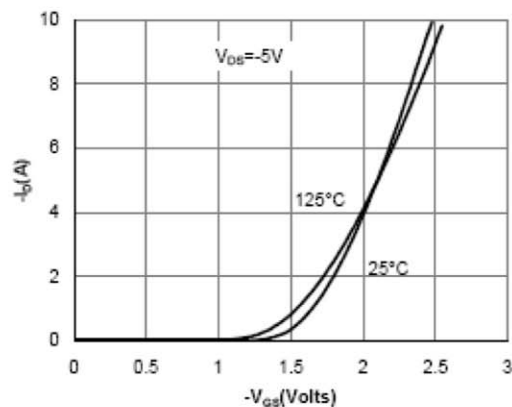


Figure 2: Transfer Characteristics

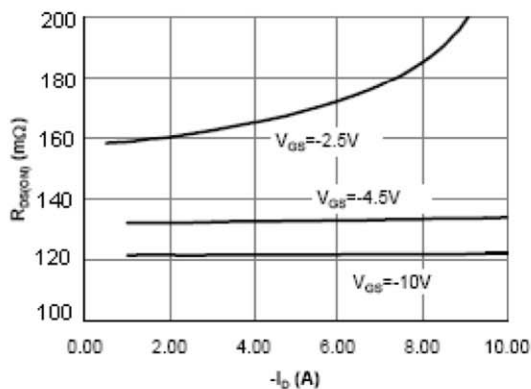


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

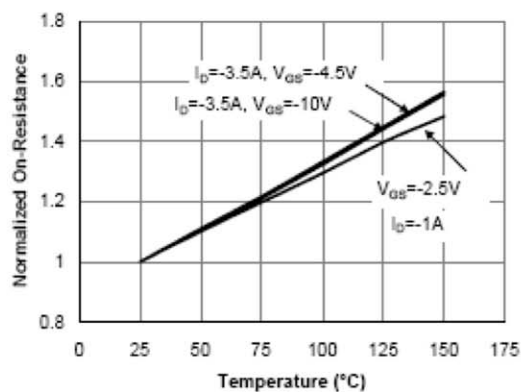


Figure 4: On-Resistance vs. Junction Temperature

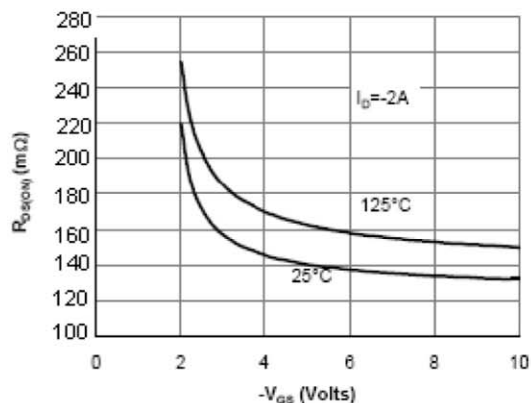


Figure 5: On-Resistance vs. Gate-Source Voltage

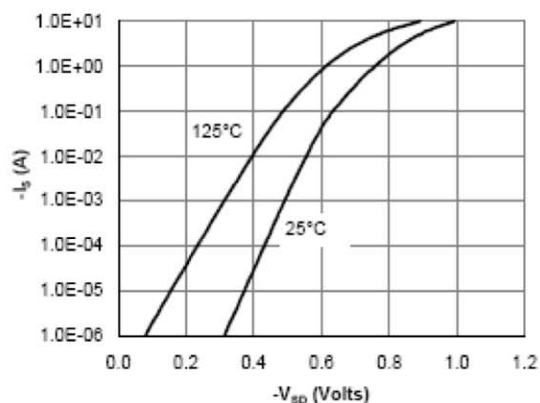


Figure 6: Body-Diode Characteristics